

Schottky barrier double diodes**PMBD352; PMBD353****FEATURES**

- Low forward voltage
- Small SMD package
- Low capacitance.

APPLICATIONS

- UHF mixer
- Sampling circuits
- Modulators
- Phase detection.

PINNING

PIN	DESCRIPTION
PMBD352 (see Fig.2)	
1	a ₁
2	k ₂
3	k ₁ , a ₂
PMBD353 (see Fig.3)	
1	k ₁
2	a ₂
3	a ₁ , k ₂

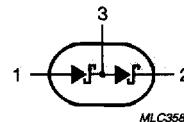


Fig.2 PMBD352 diode configuration (symbol).

DESCRIPTION

Planar Schottky barrier double diodes in series connection with different pinning.

The diodes are encapsulated in a SOT23 small plastic SMD package.

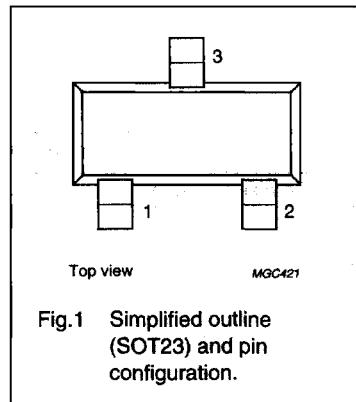


Fig.1 Simplified outline (SOT23) and pin configuration.

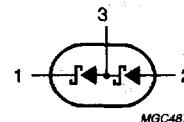


Fig.3 PMBD353 diode configuration (symbol).

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
Per diode				
V _R	continuous reverse voltage	-	4	V
I _F	continuous forward current	-	30	mA
T _{stg}	storage temperature	-65	+150	°C
T _j	junction temperature	-	100	°C

Schottky barrier double diodes**PMBD352; PMBD353****ELECTRICAL CHARACTERISTICS** $T_{amb} = 25^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V_F	forward voltage	see Fig.4 $I_F = 0.1 \text{ mA}$ $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$	350 450 600	mV mV mV
I_R	reverse current	$V_R = 3 \text{ V}$; note 1; see Fig.5	0.25	μA
C_d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 0 \text{ V}$; see Fig.6	1	pF

Note

1. Pulsed test: $t_p = 300 \mu\text{s}$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R_{thj-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Refer to SOT23 standard mounting conditions.

Schottky barrier double diodes

PMBD352; PMBD353

GRAPHICAL DATA

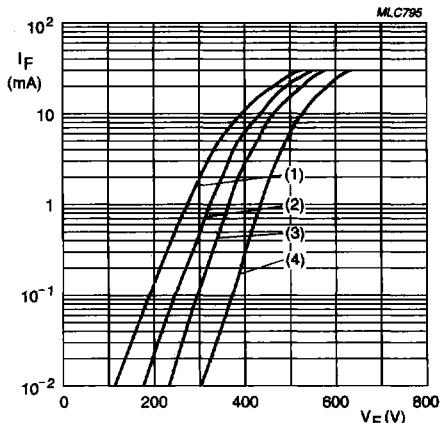


Fig.4 Forward current as a function of forward voltage; typical values.

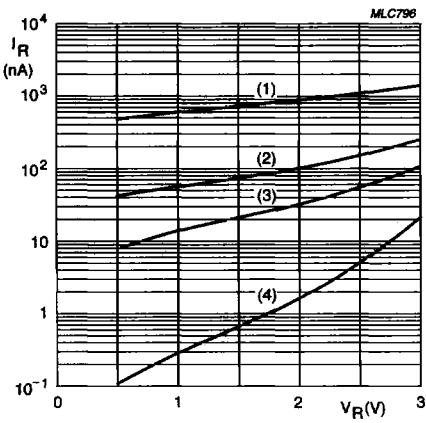


Fig.5 Reverse current as a function of reverse voltage; typical values.

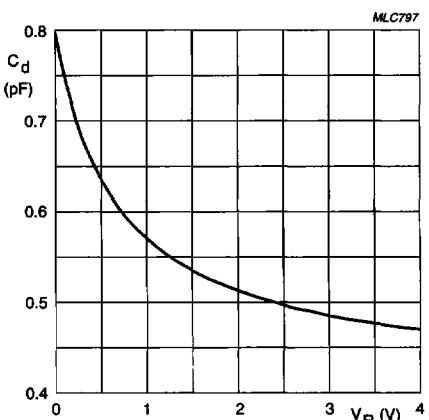


Fig.6 Diode capacitance as a function of reverse voltage; typical values.